

N-channel TrenchMOS logic level FET 12 June 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2; Fig. 3</u>		-	-	18	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	51	W
Static chara	cteristics						
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 10 A; T _j = 25 °C		-	59	69	mΩ
	resistance	V_{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C		-	-	86	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 13</u>		-	65	77	mΩ
Avalanche r	uggedness	·	,				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 18 A; V _{sup} ≤ 55 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped		-	-	33	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF 4
mb	D	mounting base; connected to drain		mbb076 S
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9277-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			
BUK9277-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9277-55A	BUK9277-55A
BUK9277-55A/CD	

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	51	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	-	18	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	13	Α

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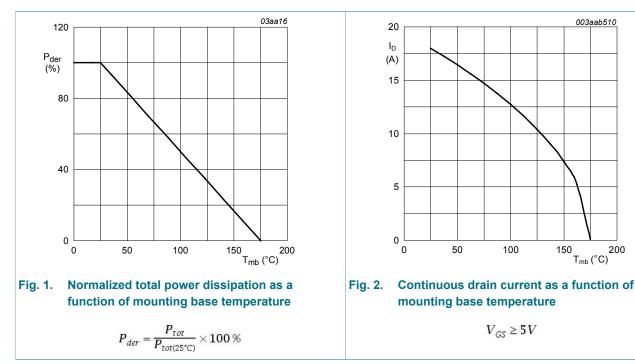
Symbol	Parameter	Conditions		Min	Max	Unit
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	73	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode		- 1			
l _S	source current	T _{mb} = 25 °C		-	18	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	73	А
Avalanche	ruggedness		- 1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 18 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$		-	33	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	<u>Fig. 4</u>	[1][2][3]	[4]	-	J

[1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

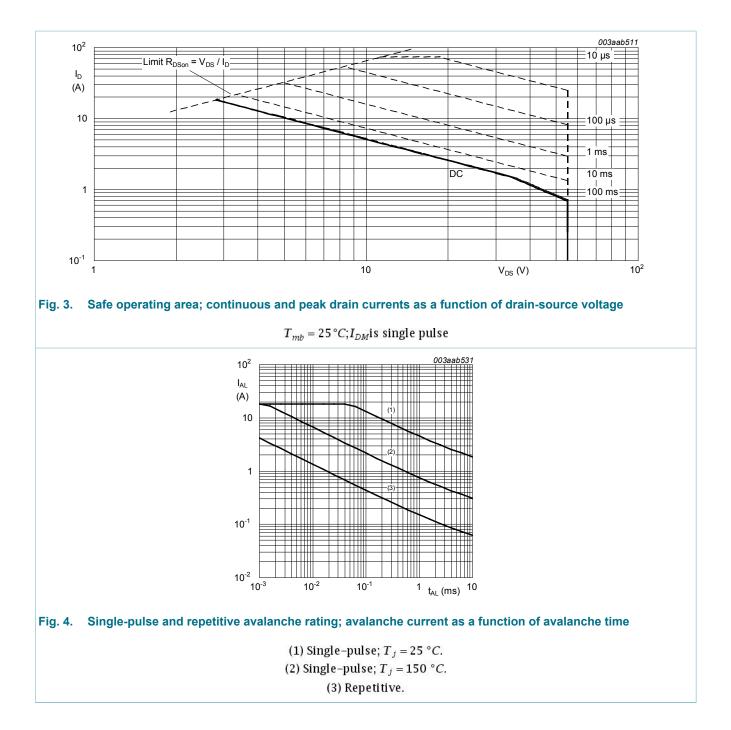
[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.



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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	2.93	K/W

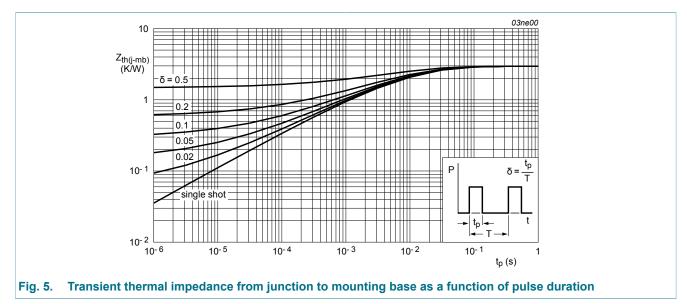
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	<u>Fig. 5</u>	-	71.4	-	K/W

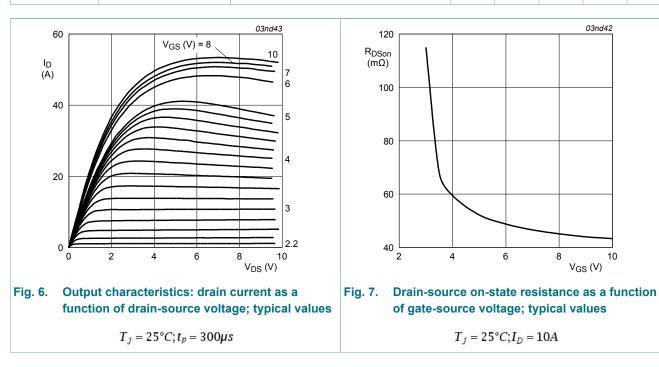


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	· · · · ·				
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
	breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 12	-	-	2.3	V
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 12	1	1.5	2	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 12	0.5	-	-	V
I _{DSS} drain leakage curre	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C	-	59	69	mΩ
n	resistance	V_{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C	-	-	86	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 13	-	-	154	mΩ

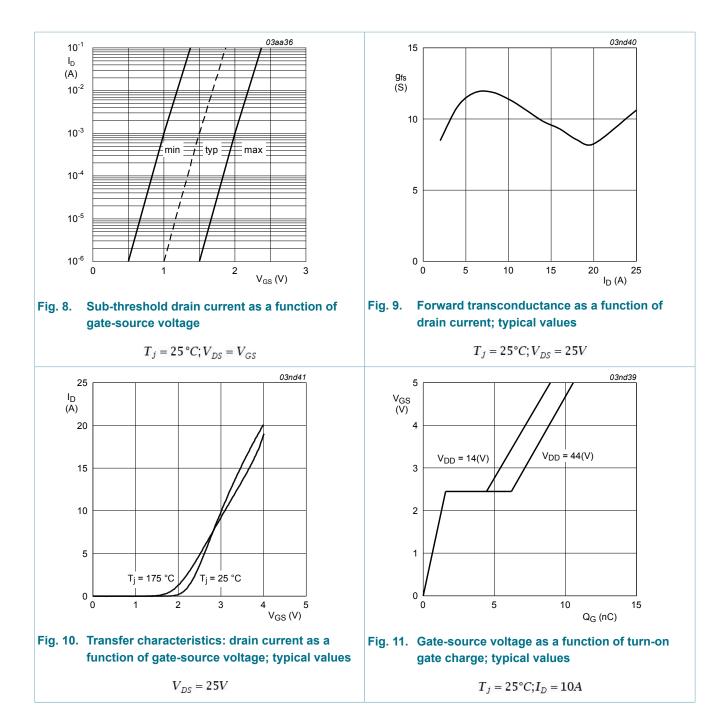
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V_{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 13</u>	-	65	77	mΩ
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	11	-	nC
Q _{GS}	gate-source charge	Fig. 14	-	1.6	-	nC
Q _{GD}	gate-drain charge		-	5	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	440	643	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	90	110	pF
C _{rss}	reverse transfer capacitance		-	60	93	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V;	-	10	-	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	47	-	ns
t _{d(off)}	turn-off delay time		-	28	-	ns
t _f	fall time		-	33	-	ns
L _D	internal drain inductance	meausured from drain lead from package to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead from package to source bond pad; T _j = 25 °C	-	7.5	-	nH
Source-dra	in diode		I			
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	33	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	60	-	nC



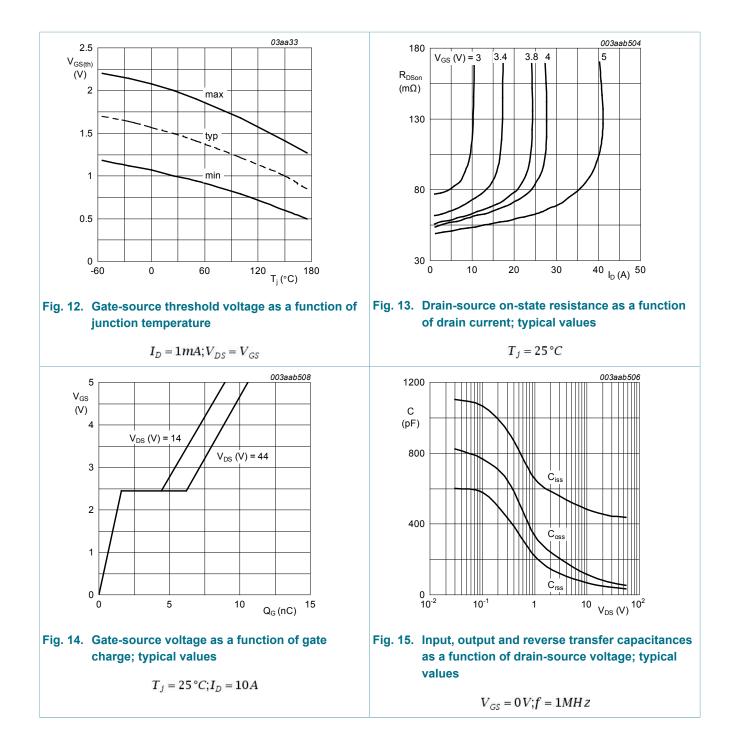
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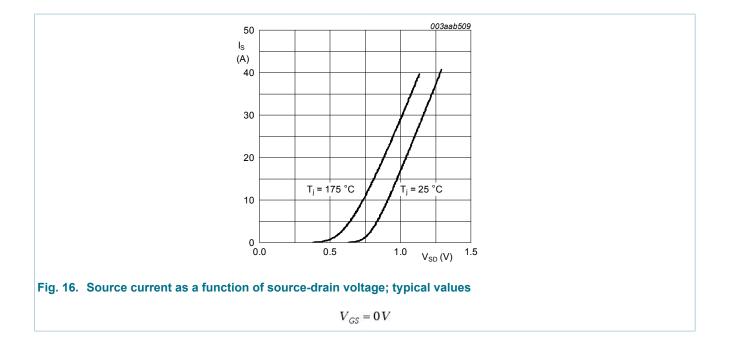
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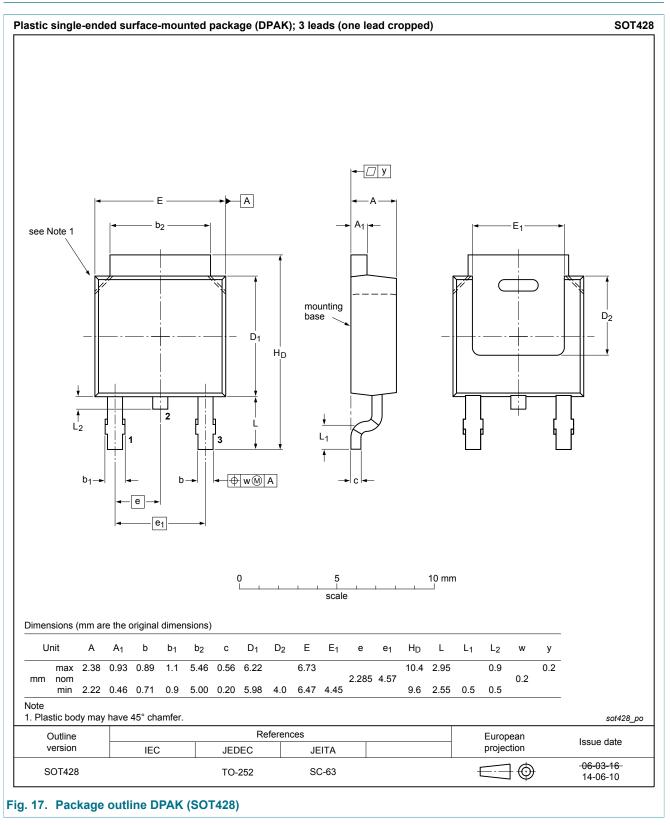
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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